

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A cleaning method of an annealed silicon wafer consisting essentially of comprising the steps of oxidizing a silicon wafer with ozonized water; ~~and~~ cleaning the oxidized silicon wafer with hydrofluoric acid~~[[,]]; and, as a final cleaning step, oxidizing the silicon wafer with ozonized water,~~ thus obtaining a silicon wafer in which micro roughness thereof under spatial frequency of $20/\mu\text{m}$ is 0.3 to 1.5 nm^3 in terms of power spectrum density.
2. (Original) The cleaning method according to claim 1, ~~further comprising wherein the steps~~ final step of oxidizing with ozonized water takes place just after the oxidation step and the hydrofluoric acid cleaning step.
3. (Currently amended) The cleaning method according to claim 1, wherein the concentration density of the ozonized water is 10 to 60 ppm.
4. (Currently amended) The cleaning method according to claim 1, wherein the concentration density of the hydrofluoric acid is 0.5 to 2%.
5. (New) The cleaning method according to claim 1, wherein an oxide film is present on the surface of the silicon wafer at the completion of the cleaning method.
6. (New) A cleaning method of an annealed silicon wafer consisting essentially of the steps of oxidizing a silicon wafer with ozonized water; cleaning the oxidized silicon wafer with hydrofluoric acid; and oxidizing the silicon wafer with ozonized water, thus obtaining a silicon wafer in which micro roughness thereof under spatial frequency of $20/\mu\text{m}$ is 0.3 to 1.5 nm^3 in terms of power spectrum density.
7. (New) The cleaning method according to claim 6, further consisting essentially of the step of oxidizing with ozonized water just after the oxidation step and the hydrofluoric acid cleaning step.

8. (New) The cleaning method according to claim 6, wherein the concentration of the ozonized water is 10 to 60 ppm.
9. (New) The cleaning method according to claim 6, wherein the concentration of the hydrofluoric acid is 0.5 to 2%.
10. (New) The cleaning method according to claim 6, wherein an oxide film is present on the surface of the silicon wafer at the completion of the cleaning method.